





12V LOW V_{CE(sat)} PNP SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching
- Ultra Small Surface Mount Package
- Lead Free, RoHS Compliant (Note 1)
- Halogen and Antimony Free "Green" Device (Note 2)
- ESD rating: 400V-MM, 8KV-HBM

Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe.
 Solderable per MIL-STD-202, Method 208
- Weight: 0.006 grams (approximate)



Top View



Top View Device Schematic



Top View Pin Out Configuration

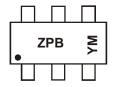
Ordering Information

Ī	Part Number	Case	Packaging
	DSL12AW-7	SOT-363	3000/Tape & Reel

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com

Marking Information



ZPB = Product Type Marking Code YM = Date Code Marking Y = Year (ex: V = 2008) M = Month (ex: 9 = September)

Date Code Key

Year	2008		2009	2010		2011	2012		2013	2014		2015
Code	V		W	X		Υ	Z		Α	В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-12	V
Collector-Emitter Voltage	V _{CEO}	-12	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current - Continuous	I _C	-2	А
Peak Pulse Collector Current	I _{CM}	-3	А

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T _A = 25°C	P _D	450	mW
Thermal Resistance, Junction to Ambient (Note 3) @ T _A = 25°C	$R_{ heta JA}$	275	°C/W
Power Dissipation (Note 4) @ T _A = 25°C	P _D	650	mW
Thermal Resistance, Junction to Ambient (Note 3) @ T _A = 25°C	$R_{ heta JA}$	192	°C/W
Operating and Storage Temperature Range	TJ, T _{STG}	-55 to +150	°C

Notes:

- 3. Device mounted on FR-4 PCB, with minimum recommended pad layout.
 4. Device mounted on FR-4 PCB, mounted on 25mmx25mm square pad 1oz coverage of copper

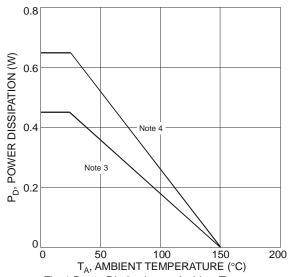
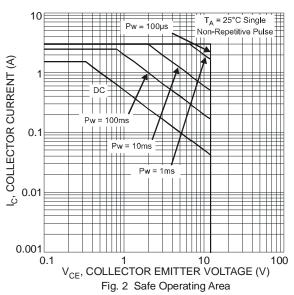


Fig. 1 Power Dissipation vs. Ambient Temperature



r(t), TRANSIENT THERMAL RESISTANCE D = 0.7 D = 0.5 D = 0.1 D = 0.05 $R_{\theta JA}(t) = r(t) * R_{\theta JA}$ $R_{\theta JA} = 188^{\circ}C/W$ D = 0.02P(pk) D = 0.01 $T_{J} - T_{A} = P * R_{\theta JA}(t)$ Duty Cycle, $D = t_1/t_2$ 0.005 0.001 1 0.1 1 10 t_1 , PULSE DURATION TIME (s) 0.00001 0.001 1,000 0.0001 0.01 100 10,000

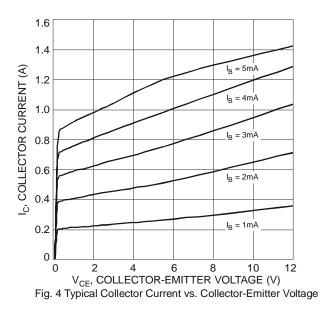
Fig. 3 Transient Thermal Response

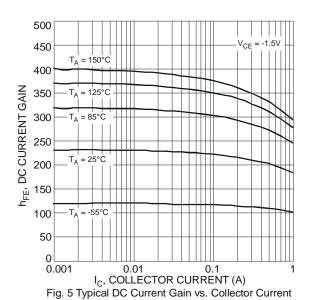


Electrical Characteristics @TA = 25°C unless otherwise specified

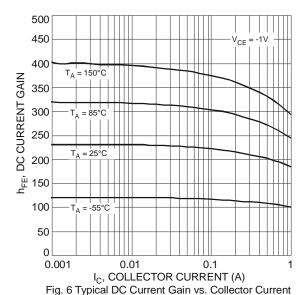
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	-12	-35	_	V	$I_C = -100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 5)	BV _{CEO}	-12	-20	_	٧	$I_C = -10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	-5	-8.3	_	V	$I_E = -100 \mu A, I_C = 0$
Collector Cutoff Current	I _{CBO}	_	-1	-100	nA	$V_{CB} = -12V, I_{E} = 0$
Collector Cutoff Current	I _{CES}	_	-1	-100	nA	$V_{CE} = -12V, V_{BE} = 0$
Emitter Cutoff Current	I _{EBO}	_	-1	-100	nA	$V_{EB} = -5V, I_C = 0$
ON CHARACTERISTICS						
DC Current Gain (Note 5)	h _{FE}	100 100 100	175 165 160	300	V	V _{CE} = -1.5V, I _C = -0.5A V _{CE} = -1.5V, I _C = -0.8A V _{CE} = -1.5V, I _C = -1A
Collector-Emitter Saturation Voltage (Note 5)	V _{CE(sat)}		-70 -95 -115	-160 -235 -290	mV	$I_C = -0.5A$, $I_B = -10mA$ $I_C = -0.8A$, $I_B = -16mA$ $I_C = -1A$, $I_B = -20mA$
Collector-Emitter Saturation Resistance	R _{CE(sat)}	_		290	mΩ	$I_C = -1A$, $I_B = -20mA$
Base-Emitter Saturation Voltage	V _{BE(sat)}	_	_	-0.95	V	$I_C = -1A$, $I_B = -20mA$
Base-Emitter Turn On Voltage	V _{BE(on)}		_	-0.95	V	$V_{CE} = -1.5V, I_{C} = -1A$
Output Capacitance	C _{obo}	_	_	65	pF	V _{CB} = -1.5V, f = 1.0MHz
Current Gain-Bandwidth Product	f _T	_	180	_	MHz	V _{CE} = -5V, I _C = -100mA, f = 100MHz

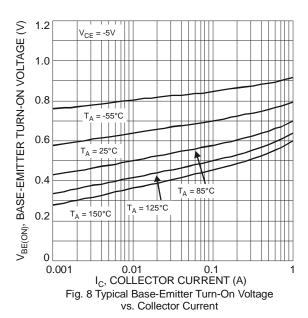
Notes: 5. Measured under pulsed conditions. Pulse width = 300μ s. Duty cycle $\leq 2\%$.

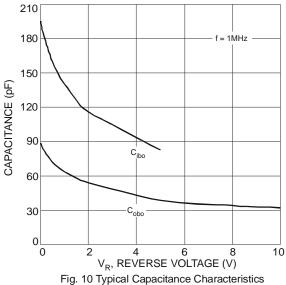












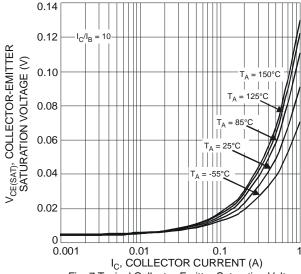
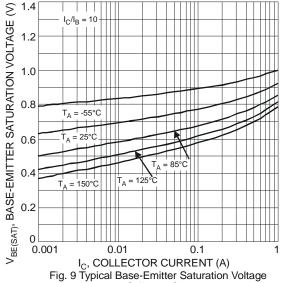


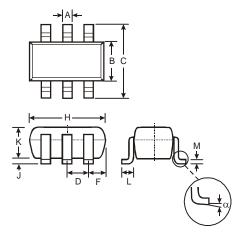
Fig. 7 Typical Collector-Emitter Saturation Voltage vs. Collector Current



vs. Collector Current

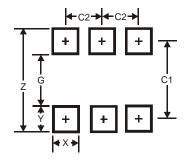


Package Outline Dimensions



	SOT-363					
Dim	Min	Max				
Α	0.10	0.30				
В	1.15	1.35				
С	2.00	2.20				
D	0.65 Typ					
F	0.40	0.45				
Н	1.80	2.20				
J	0	0.10				
K	0.90	1.00				
L	0.25	0.40				
M	0.10	0.22				
α	0°	8°				
All Dimensions in mm						

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Υ	0.6
C1	1.9
C2	0.65



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